apacitance of parallel plate capacitos with dioloctric A separation between plates. t - Thickness of chelectric slab. V1 - potential due to dielectera slab.
V2 - potential due to 200 gap.
K -> dielectric construit. C=9 9=0+ Csusface charge density) $V=V_1+V_2$, $V_1=E_m \times t$ $E_m=\frac{\sigma}{k}$ $K=\frac{E_m}{E_0}$ $V_2 = \mathcal{E}(d-t) = \frac{\sigma}{\epsilon_n}(d-t)$ V= 5(d-t)+ 5xt = 5((d-t)+t)

80 K8 $C = \frac{q}{\sqrt{\sigma(d-t(1-\frac{1}{k}))}} = \frac{\epsilon_0 A}{d-t(1-\frac{1}{k})}$ Liga P. X